

**12-BIT SHIFT REGISTER WITH OUTPUT LATCH****DESCRIPTION**

The M66320P/FP is an integrated circuit for a 12-bit serial-in parallel-out shift register with an output latch. The device can be used as a pre-driver to drive a printer head. Each output pin is capable of driving two LS TTLs.

Use of CMOS design allows the M66320P/FP to reduced power dissipation considerably compared to bipolar or Bi-CMOS products.

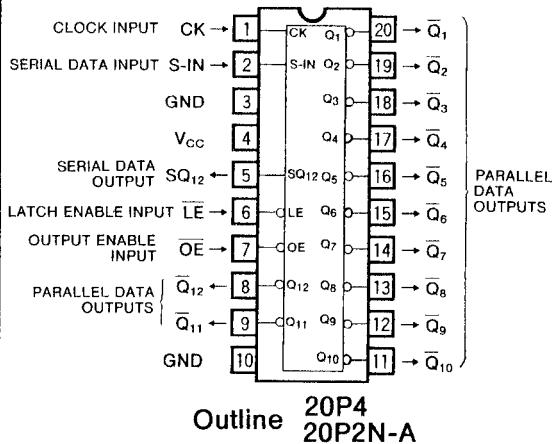
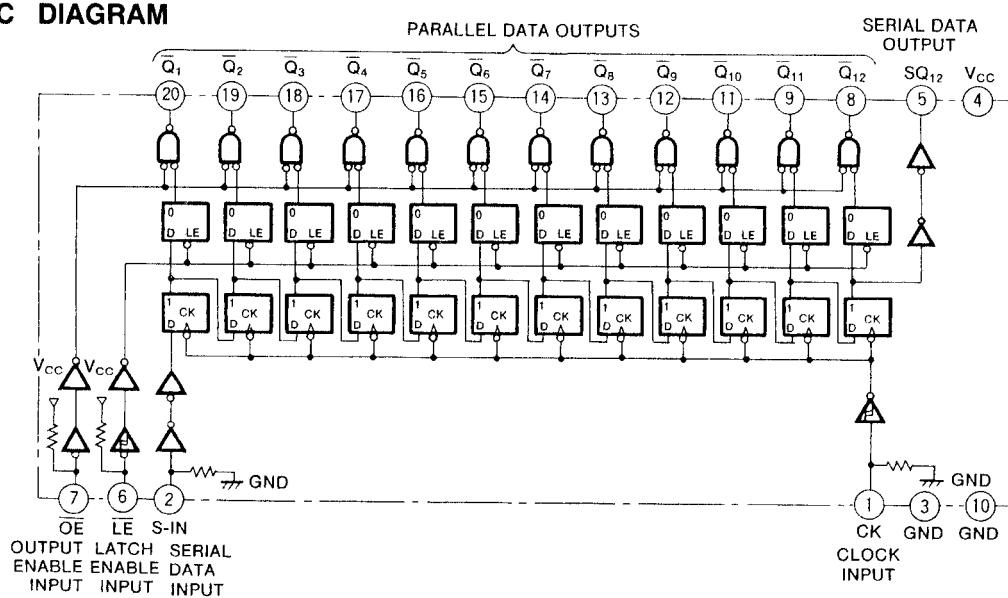
The M66320 can also be used as a serial-to-parallel data converter or for microcomputer peripheral equipment.

**FEATURES**

- Low power dissipation 100 $\mu$ W/package maximum ( $V_{CC}=5V$ ,  $T_a=25^\circ C$ , when input is open)
- Schmitt input (CK, LE)
- Wide operating temperature range  $T_a=-40\sim85^\circ C$

**APPLICATION**

Pre-driver for printer head pins.

**PIN CONFIGURATION (TOP VIEW)****LOGIC DIAGRAM**

## 12-BIT SHIFT REGISTER WITH OUTPUT LATCH

## FUNCTION

Use of a silicon-gate CMOS process allows the M66320 to maintain low power dissipation and high noise margin characteristics.

Each bit of the shift register consists of a shift flip-flop and a latch connected to the output. Shift operation takes place when the clock input changes from low-to high-level. The serial data input S-IN is the data input of the first-stage shift register, and the data S-IN shifts the shift register when CK is applied. When the S-IN is high-level, the high-level data shifts and, when the S-IN is low-level, the low-level data shifts.

The inverted data of the shift register is output to  $\bar{Q}_1 \sim \bar{Q}_{12}$ . If the latch enable input  $\bar{LE}$  is set to low-level, the contents of the shift register are latched. To expand the number of bits, use the serial data output  $SQ_{12}$  to which the content of the 12th-bit shift register is output. If the output enable input  $\bar{OE}$  is set to high-level,  $\bar{Q}_1 \sim \bar{Q}_{12}$  becomes high-level. In this case, the content of the 12th-bit shift register is output to  $SQ_{12}$ . The shift operation is not affected even if the  $\bar{OE}$  changes.

## FUNCTION TABLE (Note 1)

Inputs				Parallel outputs												Serial output $SQ_{12}$
CK	LE	S-IN	OE	$Q_1$	$\bar{Q}_2$	$Q_3$	$Q_4$	$\bar{Q}_5$	$Q_6$	$\bar{Q}_7$	$Q_8$	$\bar{Q}_9$	$Q_{10}$	$\bar{Q}_{11}$	$Q_{12}$	
↑	H	H	L	L	$Q_1^0$	$Q_2^0$	$Q_3^0$	$Q_4^0$	$Q_5^0$	$Q_6^0$	$Q_7^0$	$Q_8^0$	$Q_9^0$	$Q_{10}^0$	$Q_{11}^0$	$Q_{12}^0$
↑	H	L	L	H	$Q_1^0$	$Q_2^0$	$Q_3^0$	$Q_4^0$	$Q_5^0$	$Q_6^0$	$Q_7^0$	$Q_8^0$	$Q_9^0$	$Q_{10}^0$	$Q_{11}^0$	$Q_{12}^0$
X	L	X	L	$Q_1^0$	$Q_2^0$	$Q_3^0$	$Q_4^0$	$Q_5^0$	$Q_6^0$	$Q_7^0$	$Q_8^0$	$Q_9^0$	$Q_{10}^0$	$Q_{11}^0$	$Q_{12}^0$	$q_{12}$
X	X	X	H	H	H	H	H	H	H	H	H	H	H	H	H	$q_{12}$

Note 1 : ↑ : Change from low-to high-level

$Q^0$  : Output state Q before clock input changed

X : Irrelevant

$q^0$  : The content of shift register before clock changed

q : The content of shift register

ABSOLUTE MAXIMUM RATINGS ( $T_a = -40 \sim +85^\circ\text{C}$ , unless otherwise noted)

Symbol	Parameter		Conditions	Ratings	Unit
$V_{CC}$	Supply voltage			-0.5 ~ +7.0	V
$V_I$	Input voltage			-0.5 ~ $V_{CC} + 0.5$	V
$V_O$	Output voltage			-0.5 ~ $V_{CC} + 0.5$	V
$I_{IK}$	Input protection diode current		$V_I < 0V$	-20	mA
		$V_I > V_{CC}$	20		
$I_{OK}$	Output parasitic diode current		$V_O < 0V$	-20	mA
		$V_O > V_{CC}$	20		
$I_O$	Output current	$\bar{Q}_1 \sim \bar{Q}_{12}, SQ_{12}$		±3	mA
$I_{CC}$	Supply/GND current		$V_{CC}, GND$	±20	mA
$P_d$	Power dissipation		(Note 2)	500	mW
$T_{stg}$	Storage temperature range			-65 ~ +150	°C

Note 2 : For M66320FP, a derating of 7mW/°C should be made when  $T_a \geq 75^\circ\text{C}$

RECOMMENDED OPERATING CONDITIONS ( $T_a = -40 \sim +85^\circ\text{C}$ )

Symbol	Parameter	Limits			Unit
		Min	Typ	Max	
$V_{CC}$	Supply voltage	4.5	5	5.5	V
$V_I$	Input voltage	0		$V_{CC}$	V
$V_O$	Output voltage	0		$V_{CC}$	V
$T_{opr}$	Operating temperature range	-40		+85	°C
$t_r, t_f$	Input rise time, fall time S-IN, $\bar{OE}$	0		500	ns

## 12-BIT SHIFT REGISTER WITH OUTPUT LATCH

ELECTRICAL CHARACTERISTICS ( $V_{CC}=4.5V \sim 5.5V$ , unless otherwise noted)

Symbol	Parameter	Test conditions	Limits					Unit	
			$T_a=25^\circ C$			$T_a=-40 \sim +85^\circ C$			
			Min	Typ	Max	Min	Max		
$V_{IH}$	High-level input voltage S-IN, $\overline{OE}$	$V_o=0.1V, V_{CC}=0.1V$ $ I_o =20\mu A$	0.70×V <sub>CC</sub>			0.70×V <sub>CC</sub>		V	
$V_{IL}$	Low-level input voltage S-IN, $\overline{OE}$	$V_o=0.1V, V_{CC}=0.1V$ $ I_o =20\mu A$			0.30×V <sub>CC</sub>		0.30×V <sub>CC</sub>	V	
$V_{T+}$	Positive threshold voltage CK, $\overline{LE}$	$V_o=0.1V, V_{CC}=0.1V$ $ I_o =20\mu A$	0.35×V <sub>CC</sub>		0.8×V <sub>CC</sub>	0.35×V <sub>CC</sub>	0.8×V <sub>CC</sub>	V	
$V_{T-}$	Negative threshold voltage CK, $\overline{LE}$	$V_o=0.1V, V_{CC}=0.1V$ $ I_o =20\mu A$	0.2×V <sub>CC</sub>		0.65×V <sub>CC</sub>	0.2×V <sub>CC</sub>	0.65×V <sub>CC</sub>	V	
$V_{OH}$	High-level output voltage $Q_1 \sim Q_{12}, SQ_{12}$	$V_i=V_{T+}, V_{T-}$ $V_{CC}=4.5V$ $I_{OH}=-20\mu A$	$V_{CC}-0.1$			$V_{CC}-0.1$		V	
$V_{OL}$	Low-level output voltage $Q_1 \sim Q_{12}, SQ_{12}$	$V_i=V_{T+}, V_{T-}$ $V_{CC}=4.5V$ $I_{OL}=20\mu A$	4.1			4.0		V	
$I_{CC}$	Static supply current	When input is open, $V_{CC}=5.5V$ $V_i=V_{CC}, GND, V_{CC}=5.5V$			20.0		200.0	$\mu A$	
					1.5		2.2	mA	

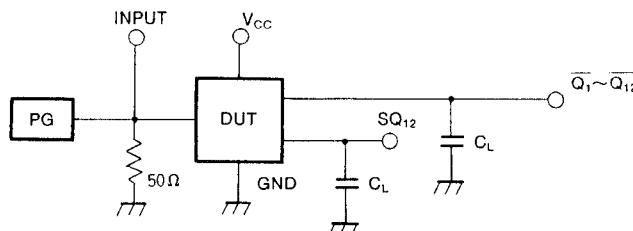
SWITCHING CHARACTERISTICS ( $V_{CC}=5V$ )

Symbol	Parameter	Test conditions	Limits					Unit	
			$T_a=25^\circ C$			$T_a=-40 \sim +85^\circ C$			
			Min	Typ	Max	Min	Max		
$f_{max}$	Maximum repetitive frequency		3			2.5		MHz	
$t_{PLH}$	Low-to high-level and high-to low-level output propagation time from CK to $SQ_{12}$				300		400	ns	
$t_{PHL}$	Low-to high-level and high-to low-level output propagation time from CK to $\overline{Q}_1 \sim \overline{Q}_{12}$				300		400	ns	
$t_{PLH}$	Low-to high-level and high-to low-level output propagation time from $\overline{OE}$ to $\overline{Q}_1 \sim \overline{Q}_{12}$				300		400	ns	
$t_{PHL}$	Low-to high-level and high-to low-level output propagation time from $\overline{LE}$ to $\overline{Q}_1 \sim \overline{Q}_{12}$				300		400	ns	
$t_{PLH}$	Low-to high-level and high-to low-level output propagation time from CK to $SQ_{12}$	$C_L=15pF$ (Note 3)			300		400	ns	
$t_{PHL}$	Low-to high-level and high-to low-level output propagation time from CK to $\overline{Q}_1 \sim \overline{Q}_{12}$				300		400	ns	
$t_{PLH}$	Low-to high-level and high-to low-level output propagation time from $\overline{OE}$ to $\overline{Q}_1 \sim \overline{Q}_{12}$				300		400	ns	
$t_{PHL}$	Low-to high-level and high-to low-level output propagation time from $\overline{LE}$ to $\overline{Q}_1 \sim \overline{Q}_{12}$				300		400	ns	

TIMING REQUIREMENTS ( $V_{CC}=5V$ )

Symbol	Parameter	Test conditions	Limits					Unit	
			$T_a=25^\circ C$			$T_a=-40 \sim +85^\circ C$			
			Min	Typ	Max	Min	Max		
$t_w$	CK pulse width		160			200		ns	
$t_{SU}$	S-IN setup time with respect to CK		80			100		ns	
$t_h$	S-IN hold time with respect to CK		80			100		ns	

Note 3 : Test circuit



- (1) The pulse generator (PG) has the following characteristics (10%~90%) :  $t_r=6ns, t_f=6ns$   
(2) The capacitance  $C_L$  includes stray wiring capacitance and the probe input capacitance.

**12-BIT SHIFT REGISTER WITH OUTPUT LATCH****TIMING DIAGRAM**